

SPECIFICATION AMENDMENTS:

Please replace the paragraph on page 1, lines 5 through 7, with the following amended paragraph:

--The invention relates to a method of fabricating a semiconductor device having trenches which are used for isolating elements, and particularly relates to a method of rounding a cornered portion of each trench.--

Please replace the paragraph on page 1, lines 13 through 18, with the following amended paragraph:

--The STI method is a method of realizing isolating of elements by forming trenches on a semiconductor substrate and filling an insulating film inside the trenches. According to this STI method, isolating areas are formed up to the depth of the semiconductor substrate so that each width of the isolating areas can be narrowed compared with that formed by the LOCOS method.--

Please replace the paragraph bridging pages 5 and 6 with the following amended paragraph:

--First to fourth embodiments of the invention are now described with reference to Figs. 1 to 6. Each figure shows a step representing a method of fabricating a semiconductor device of the invention by way of section of examples of configurations thereof. Each figure merely schematically shows the shape,

size, arrangement of each component to the extent that the skilled person can understand the invention, and the invention is not limited to the illustrated examples. For brevity of understanding the figures, hatching for showing the cross section is omitted except for a part thereof. Although a specific material, and condition and the like are used in the following ~~explanation~~ but explanation, such a material and condition is but one of preferred examples, and hence the invention is not limited thereto. The same components in each figure are depicted by the same reference numerals and the overlapped explanation thereof may be omitted.--

Please replace the paragraph on page 7, lines 12 through 15, with the following amended paragraph:

--Thereafter, a resist film is formed ~~in the~~ having a film thickness of 200 nm on the entire surface of the silicon nitride film 14 using a CVD process, then the resist film is subjected to a photolithography step to form masks 16 for forming trenches of in the silicon substrate 10 by patterning.--

Please replace the paragraph on page 8, lines 4 through 7, with the following amended paragraph:

--In such a manner, irregularities are formed on the silicon substrate 10,

thereby forming trenches 18 which are recessed portions each having a depth of about 500 nm. The mask 16 for forming trenches are is removed after forming the trenches 18.--

Please replace the paragraph on page 9, lines 13 through 16, with the following amended paragraph:

--As shown in Fig. 2B, an ~~oxide~~ oxide treatment is subjected to the surface of the silicon substrate 10 for forming the trenches 18, e.g., by use of a thermal oxidation process using dry oxygen at the temperature of 1100°C, i.e., by use of a high temperature dry oxidation process.--

Please replace the paragraph bridging pages 9 and 10 with the following amended paragraph:

--In the oxide treatment, oxygen (O₂) is supplied to the silicon substrate 10 from the upper side of the silicon oxide film 22 and it is diffused in the silicon oxide film 22. Accordingly, oxidative reaction is started at the first cornered portion 18c which is the closest to a diffusion ~~source, thereafter,~~ source. Thereafter, the oxidation gradually develops from the first cornered portion 18c toward the side wall portion 18b and a convex portion 18d of the silicon substrate 10 which is covered with the silicon oxide film 12. Further, since the oxidative

reaction slowly develops under a high temperature atmosphere in this configuration, viscous flow of the oxide film becomes large.--